

# SLLIMM -nano 2<sup>nd</sup> series

## Intelligent Power Modules



#### Boost the power capability and save space in Home Appliance applications

The new SLLIMM\*-nano 2<sup>nd</sup> series of IGBT and SJ-MOSFET based intelligent power modules fully satisfies space saving needs and features required in power applications working at up to 500 W.

The SJ-MOSFET based products, with a  $R_{DS(on)}$  up to 1  $\Omega$ , are the ideal choice for fridge compressors and all applications working at low load. The IGBT based products, are ideal choice for full load applications, addressing also low-power washing machines.

#### **KEY FEATURES**

- 600 V SJ-MOSFET and IGBT (planar and TFS) based IPMs
- Current capability from 1 up to 8 A at 25 °C
- Optimized voltage drop in conduction
- On-board NTC thermistor
- Slots for heatsink screws
- Dual-inline or zig-zag leads
- With and without stand off
- UL recognized 1.5 kVrms: UL 1557, file E81734

#### **KEY BENEFITS**

- Higher robustness and reliability
- Package compactness and thermal performance
- Embedded protection inside the module
- Plug'n Play solution
- · Easily driven by microcontroller

#### MAIN APPLICATIONS

- Fans
- Dishwashers
- Compressors
- Pumps
- Refrigerators
- Washing machine

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To highlight the advantages of our IPMs, we compared their performance under two different conditions corresponding to a fridge compressor and washing machine.

**Figure 1** shows that our SJ-MOSFET IPM works better than IGBT IPM up to 100 W, having a lower delta temperature  $(T_{case} - T_{amb})$ , thus maximizing efficiency at low loads.

**Figure 2** shows a benchmark with our IGBT based IPM vs the main competitor, revealing a better performance across the entire frequency range typical of washing machine conditions.

### Fig1: IGBT vs SJ-MOSFET IPMs, low load delta temperature vs input power







Part number	Switch type	BV	I <sub>cn</sub>	R <sub>DS(ON)</sub> max @ I <sub>CN/2</sub> V <sub>cesat</sub> typ @ I <sub>CN</sub>	t <sub>dead min</sub>
STIPQ3M60T-HZ/L	SJ-MOSFET	600 V	3 A	1.6 Ω	1 µs
STIPQ5M60T-HZ/L			5 A	1 Ω	1 µs
STGIPQ3H60T-HZ/L(S)	Planar IGBT		3 A	2.15 V	1.5 µs
STGIPQ3HD60-HZ/L			3 A	2.15 V	1 µs
STGIPQ4C60T-HZ/L	TFS IGBT		3 A	1.6 V	1.5 µs
STGIPQ5C60T-HZ/L(S)			5 A	1.65 V	1.5 µs
STGIPQ8C60T-HZ			8 A	2 V	1 µs

#### NOMENCLATURE





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